

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: S. NAGAHAMA et al. Conf.: Unassigned  
Appl. No.: NEW - Div. of U.S. Group: Unassigned  
Appl. 09/714,143  
Filed: June 24, 2003 Examiner: UNASSIGNED  
For: NITRIDE SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT  
(SUBMISSION WITH CONTINUATION-IN-PART OR  
RULE 1.53(b) CONTINUATION OR DIVISIONAL APPLICATION)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 24, 2003

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications, or other information submitted for consideration by the Office are listed on the PTO-1449 form(s), attached hereto.

II. REFERENCES PREVIOUSLY CITED OR SUBMITTED

Pursuant to 37 C.F.R. § 1.98(d), consideration of information listed on the PTO-1449 form(s) is requested since any patents, publications, or other information which are listed on the PTO-1449 form(s) but for which copies are not enclosed herewith, were previously cited by or submitted to the PTO in one of the following applications which has been relied upon for an earlier filing date under 35 U.S.C. § 120:

U.S. Appl. No(s).  
09/714,143  
09/004,925

U.S. Filing Date(s)  
November 17, 2000  
January 9, 1998

III. FEES


This Information Disclosure Statement is being filed concurrent with the filing of a continuation-in-part, continuation, or divisional patent application; therefore, no fee is required.

If the Examiner has any questions concerning this IDS or requires a copy of any of the references cited but not provided, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule and charge the appropriate fee to Deposit Account No. 02-2448.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By   
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Attachment(s) : ☒ PTO-1449(s)

☒ References (1)

☐ Foreign Search Report

☐ Other:

(Rev. 04/29/03)

Form PTO-1449				ATTY DOCKET NO. 0020-5123P		APPLICATION NO. NEW - Div. of 09/714,143		
<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (Use several sheets if necessary)				APPLICANT S. NAGAHAMA et al.				
				FILING DATE June 24, 2003		GROUP Unassigned		
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER INITIAL	DOCUMENT NUMBER	Kind	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
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	US 5,306,662	A	1994-04-26	Nakamura et al.				
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	US 5,585,648	A	1996-12-17	Tischler				
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<b>FOREIGN PATENT DOCUMENTS</b>								
Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
JP	9-116234	A	1997-05-02	JAPAN			abs	
JP	2-288371	A	1990-11-28	JAPAN			abs	
<b>OTHER DOCUMENTS</b> (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)								
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EXAMINER				DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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<b>FOREIGN PATENT DOCUMENTS</b>								
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	GB	2 298 735	A	1996-09-11	GREAT BRITAIN			X
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<b>OTHER DOCUMENTS</b> (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)								
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								YES	NO
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	JP	9-298341	A	1997-11-18	JAPAN			X	
	JP	8-070139	A	1996-03-12	JAPAN			X	
<b>OTHER DOCUMENTS</b> (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)									
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